10/518945

DT05 Rec'd PCT/PTO 0 9 DEC 2004

VIA Express Mail EL629610319US PATENT 36856.1310

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re. application of:

Yoshihiro ITO and Michio KADOTA

Serial No.: Unknown

Filed: Concurrently herewith

For: SEMICONDUCTOR DEVICE AND

METHOD FOR MANUFACTURING

SEMICONDUCTOR DEVICE

International Application No.:

PCT/JP03/07055

International Filing Date:

June 4, 2003

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

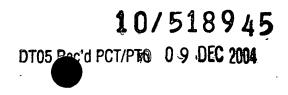
Sir:

In accordance with 37 CFR §1.56, and in recognition of their duty to disclose to the United States Patent and Trademark Office relevant information known to be material to patentability, Applicants herewith submit copies of the prior art listed on the attached Form PTO-1449. The prior art references No. 1-6 and 8-11 were cited in the International Search Report for PCT Application No. PCT/JP03/07055. The prior art references No. 7, 12, and 13 are additional references that Applicants are submitting herewith.

The relevance of the prior art reference No. 7 is discussed on page 3 of the substitute specification filed concurrently herewith.

The relevance of the prior art reference 12 is discussed on page 2 of the substitute specification filed concurrently herewith.

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Statement
December 9, 2004
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The relevance of the prior art reference 13 is discussed on pages 2 and 3 of the substitute specification filed concurrently herewith.

The statement is not a representation that all of the information cited is necessarily effective as prior art against the application.

Applicants respectfully request that the disclosed references be made of record in the subject application.

Respectfully submitted,

Date: December 9, 2004

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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

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Sheet	1	of	2

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Application Number				
Filing Date				
First Named Inventor	Yoshihiro ITO			
Art Unit				
Examiner Name				
Attorney Docket Number	36856.1310			

	U.S. PATENT DOCUMENTS						
Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where		
Initials*	No.1	Number-Kind Code ^{2(if known)}	MM -YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear		
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		FO	REIGN PATEN	T DOCUMENTS		
Examine r Initials*	Cite No.1	Foreign Patent Document Country Code ³ Number-Kind Code ⁵ (if known)	Publication Date MM -YYYY	Country of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Le
	1	JP 2002-326895 (English abstract and machine translation)	11/2002	JAPAN		x
	2	JP 2001-244464 (English abstract and machine translation)	09/2001	JAPAN		х
	3	JP 2000-150900 (English abstract and machine translation)	05/2000	JAPAN		х
	4	JP 2002-319682 (English abstract and machine translation	10/2002	JAPAN		х
	5	JP 10-306372 (English abstract and machine translation	11/1998	JAPAN		х
	6	EP 1 134 811	09/2001	EPO	1	х
***************************************	7	JP 05-171435 (English abstract and machine translation	07/1993	JAPAN		x
	8	JP 2001-144328 (English abstract and machine translation	05/2001	JAPAN		x

^{*}Examiner: Initial if reference considered, whether of not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant.

¹ Applicant unique citation designation number (optional). ²See Kind Codes of USPTO Patent documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document by the two-letter code (WIPO Strandard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Abstract is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14.

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•				First Named Inventor	Yoshihiro ITO	
STATEMENT BY APPLICANT		NT	Art Unit			
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Sheet	2	of	2		Attorney Docket Number	36856.1310
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		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title Of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	9	Yutaka OHYA et al., "THIN FILM TRANSISTOR OF ZnO FABRICATED BY CHEMICAL SOLUTION DEPOSITION", Jpn. J. Appl. Phys., Vol. 40 (2001), pp. 297-298, Part 1, No. 1, January 2001.	
	10	K. YAMAYA et al., "USE OF HELICON-WAVE EXCITED PLASMA FOR ALUMINUM-DOPED ZnO THIN-FILM SPUTTERING", Appl. Phys. Lett. 72 (2), January 12, 1998, pp. 235-237.	
	11	S.K. HONG et al., "ZnO AND RELATED MATERIALS: PLASMA-ASSISTED MOLECULAR BEAM EPITAXIAL GROWTH, CHARATERIZATION, AND APPLICATION", Journal of Electronic Materials, Vo. 30, No. 6, 2001, pp. 647-658.	
	12	Shen ZHU et al., "POLARITY EFFECTS OF SUBSTRATE SURFACE IN HOMOEPITAXIAL ZnO FILM GROWTH", Journal of Crystal Growth 219 (2000), pp. 361-367.	
	13	Yefan CHEN et al., "MORPHOLOGY EVOLUTION OF ZnO (000 1) SURFACE DURING PLASMA-ASSISTED MOLECULAR-BEAM EPITAXY", Applied Physics Letters, Volume 80, Numbe 8, 02/2002, pp. 1358-1360.	
	14	Soon-Ku HONG et al., "CONTROL OF POLOARITY OF ZnO FILMS GROWN BY PLASMA-ASSISTED MOLECULAR-BEAM EPITAXY: Zn- AND O-POLAR ZnO FILMS ON Ga-POLAR AND GaN TEMPLATES", Applied Physics Letters, Volume 77, Number 22, 11/2000, pp. 3571-3573.	
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Examiner	Date	
Signature	Considered	

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